## DATA SHEET



# BAS55 <br> High－speed diode 

Product specification
Supersedes data of April 1996
File under Discrete Semiconductors，SC01

## FEATURES

- Small plastic SMD package
- High switching speed: max. 6 ns
- Continuous reverse voltage: max. 60 V
- Repetitive peak reverse voltage: max. 60 V
- Repetitive peak forward current: max. 600 mA .


## APPLICATIONS

- High-speed switching in surface mounted circuits.


## DESCRIPTION

The BAS55 is a high-speed switching diode fabricated in planar technology, and encapsulated in the small rectangular plastic SMD SOT23 package.

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | anode |
| 2 | not connected |
| 3 | cathode |



MAM185

Marking code: L5p.
Fig. 1 Simplified outline (SOT23) and symbol.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\text {RRM }}$ | repetitive peak reverse voltage |  | - | 60 | V |
| $\mathrm{~V}_{R}$ | continuous reverse voltage |  | - | 60 | V |
| $\mathrm{I}_{\mathrm{F}}$ | continuous forward current | see Fig.2; note 1 | - | 250 | mA |
| $\mathrm{I}_{\text {FRM }}$ | repetitive peak forward current |  | - | 600 | mA |
| $\mathrm{I}_{\text {FSM }}$ | non-repetitive peak forward current | square wave; $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ prior to <br> surge; see Fig.4 <br>  | $\mathrm{t}=1 \mu \mathrm{~s}$ <br> $\mathrm{t}=100 \mu \mathrm{~s}$ <br> $\mathrm{t}=10 \mathrm{~ms}$ |  |  |

## Note

1. Device mounted on an FR4 printed-circuit board.

## ELECTRICAL CHARACTERISTICS

$\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{F}}$ | forward voltage | see Fig.3; $\mathrm{I}_{\mathrm{F}}=200 \mathrm{~mA}$; DC value; note 1 | - | 1.0 | V |
| $\mathrm{I}_{\mathrm{R}}$ | reverse current | $\begin{aligned} & \text { see Fig. } 5 \\ & \quad V_{R}=60 \mathrm{~V} \\ & V_{R}=60 \mathrm{~V} ; \mathrm{T}_{j}=150^{\circ} \mathrm{C} \\ & \hline \end{aligned}$ |  | $\begin{aligned} & 100 \\ & 100 \\ & \hline \end{aligned}$ | $\begin{array}{\|l\|} \mathrm{nA} \\ \mu \mathrm{~A} \\ \hline \end{array}$ |
| $\mathrm{C}_{\mathrm{d}}$ | diode capacitance | $\mathrm{f}=1 \mathrm{MHz} ; \mathrm{V}_{\mathrm{R}}=0$; see Fig. 6 | - | 2.5 | pF |
| $\mathrm{t}_{\mathrm{rr}}$ | reverse recovery time | when switched from $I_{F}=400 \mathrm{~mA}$ to $\mathrm{I}_{\mathrm{R}}=400 \mathrm{~mA} ; \mathrm{R}_{\mathrm{L}}=100 \Omega$; measured at $\mathrm{I}_{\mathrm{R}}=40 \mathrm{~mA}$; see Fig. 7 | - | 6 | ns |
| $\mathrm{V}_{\text {fr }}$ | forward recovery voltage | when switched to $\mathrm{I}_{\mathrm{F}}=400 \mathrm{~mA}$; $\mathrm{t}_{\mathrm{r}}=30 \mathrm{~ns}$; see Fig. 8 | - | 2 | V |
|  |  | when switched to $\mathrm{I}_{\mathrm{F}}=400 \mathrm{~mA}$; $\mathrm{t}_{\mathrm{r}}=100 \mathrm{~ns}$; see Fig. 8 | - | 1.5 | V |

## Note

1. $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$; device has reached the thermal equilibrium when mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
| :--- | :--- | :--- | :---: | :---: |
| $\mathrm{R}_{\text {th j } \mathrm{jp}}$ | thermal resistance from junction to tie-point |  | 330 | $\mathrm{~K} / \mathrm{W}$ |
| $\mathrm{R}_{\text {th j }-\mathrm{a}}$ | thermal resistance from junction to ambient | note 1 | 500 | $\mathrm{~K} / \mathrm{W}$ |

## Note

1. Device mounted on an FR4 printed-circuit board.

## GRAPHICAL DATA



Device mounted on an FR4 printed-circuit board.
Fig. 2 Maximum permissible continuous forward current as a function of ambient temperature.


Fig. 3 Forward current as a function of forward voltage; typical values.


Fig. 4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.
(2) $\mathrm{V}_{\mathrm{R}}=60 \mathrm{~V}$; typical values.
Fig. 5 Reverse current as a function of junction temperature.

$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$.
Fig. 6 Diode capacitance as a function of reverse voltage; typical values.


Fig. 7 Reverse recovery voltage test circuit and waveforms.


## PACKAGE OUTLINE



Fig. 9 SOT23.

## DEFINITIONS

| Data Sheet Status |  |
| :--- | :--- |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values |  |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or <br> more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation <br> of the device at these or at any other conditions above those given in the Characteristics sections of the specification <br> is not implied. Exposure to limiting values for extended periods may affect device reliability. |  |
| Application information |  |
| Where application information is given, it is advisory and does not form part of the specification. |  |

## LIFE SUPPORT APPLICATIONS

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